N-Channel 80-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

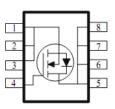
- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
80	$35 @ V_{GS} = 10V$	9		
80	40 @ V _{GS} = 4.5V	8		



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Limit	Units					
Drain-Source Voltage			80	V				
Gate-Source Voltage		V_{GS}	±20	V				
Continuous Drain Current ^a	T _A =25°C	· I _D	9					
Continuous Diain Current	T _A =70°C	טי	7	Α				
Pulsed Drain Current ^b		I _{DM}	50					
Continuous Source Current (Diode Conduction) a		I _S	4	Α				
Power Dissipation ^a	T _A =25°C	P _D	3.5	W				
Fower Dissipation	T _A =70°C	' D	2	VV				
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C				

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

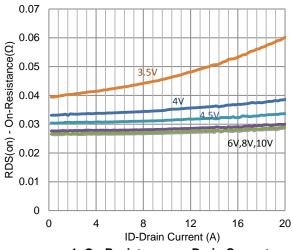
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Brain Guirent	טטי	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	4.5			Α	
Drain-Source On-Resistance	r _{no()}	$V_{GS} = 10 \text{ V}, I_D = 7.2 \text{ A}$			35	35 mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 7.1 \text{ A}$			40	11177	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 7.2 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 2 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
		Dynamic					
Total Gate Charge	Q_g			17			
Gate-Source Charge	Q_gs	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 7.2 \text{ A}$		4.8		nC	
Gate-Drain Charge	Q_gd			9.2			
Turn-On Delay Time	t _{d(on)}			4			
Rise Time	t _r	$V_{DS} = 40 \text{ V}, R_L = 5.6 \Omega, I_D = 7.2 \text{ A},$		8		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		48		ns	
Fall Time	t _f			19			
Input Capacitance	C_{iss}			1216			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		154		pF	
Reverse Transfer Capacitance	C_{rss}			131			

Notes

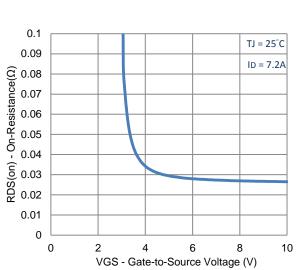
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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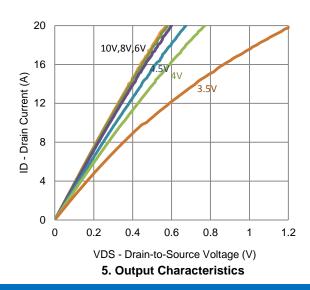
Typical Electrical Characteristics

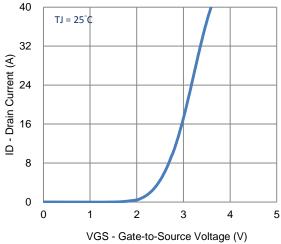


1. On-Resistance vs. Drain Current

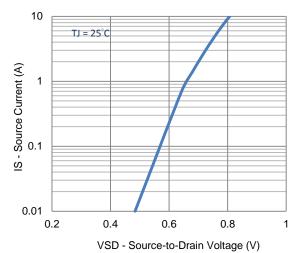


3. On-Resistance vs. Gate-to-Source Voltage

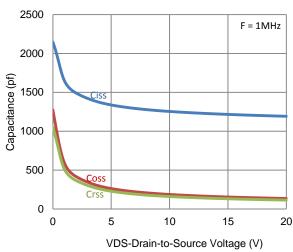




2. Transfer Characteristics

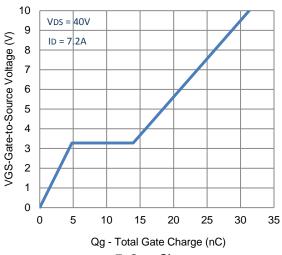


4. Drain-to-Source Forward Voltage

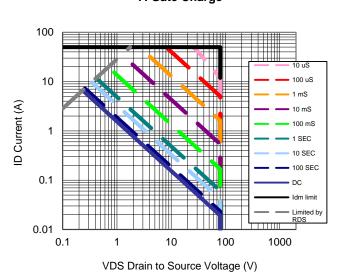


6. Capacitance

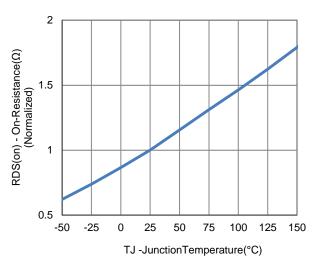
Typical Electrical Characteristics



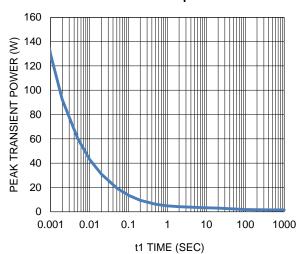
7. Gate Charge



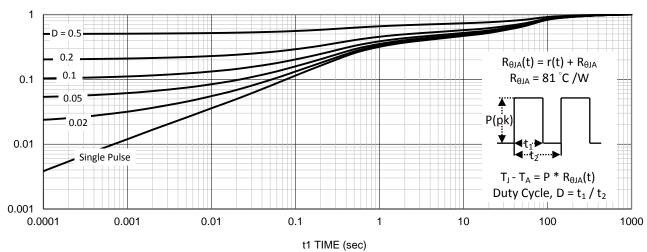
9. Safe Operating Area



8. Normalized On-Resistance Vs Junction Temperature

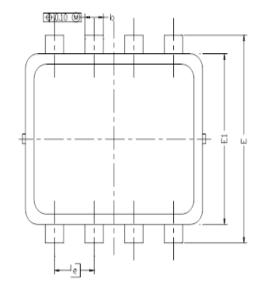


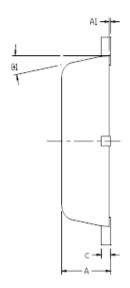
10. Single Pulse Maximum Power Dissipation

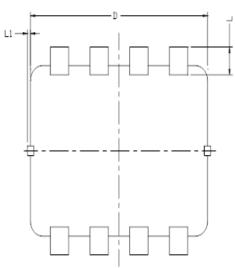


11. Normalized Thermal Transient Junction to Ambient

Package Information







DIM.	MILLIMETERS			INCHES			
וייונע	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0,00		0,05	0,000		0,002	
b	0.24	0.30	0,35	0.009	0.012	0.014	
_	0.08	0.152	0.25	0.003	0,006	0.010	
D	(2	2.90 BSC			0.114 BSC		
E	2	2,80 BS	С	0.110 BSC			
E1	2	2.30 BSC			0.091 BSC		
9	0	0,65 BSC			0.026 BSC		
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0	10	12	0	10	12	